

# ST13003, ST13003-K

## High voltage fast-switching NPN power transistor



### Figure 1. Internal schematic diagram



### Datasheet - production data

### **Features**

- High voltage capability
- Low spread of dynamic parameters
- Very high switching speed

### **Applications**

- Electronic ballast for fluorescent lighting (CFL)
- SMPS for battery charger

### Description

The device is manufactured using high voltage multi-epitaxial planar technology for high switching speeds and high voltage capability.

It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

#### Table 1. Device summary

Part number	Marking	Package	Packaging
ST13003	13003	SOT-32	Tube
ST13003-K	13003	SOT-32	Bag

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This is information on a product in full production.

# 1 Electrical ratings

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage (V <sub>BE</sub> = 0)	700	V
$V_{CEO}$	Collector-emitter voltage (I <sub>B</sub> = 0)	400	V
$V_{\text{EBO}}$	Emitter-base voltage (I <sub>C</sub> = 0, I <sub>B</sub> = 0.75 A, t <sub>P</sub> < 10 $\mu$ s)	V <sub>(BR)EBO</sub>	V
۱ <sub>C</sub>	Collector current	1.5	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	3	А
Ι <sub>Β</sub>	Base current	0.75	А
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms)	1.5	А
P <sub>TOT</sub>	Total dissipation at $T_{C}$ = 25 °C	40	W
T <sub>STG</sub>	Storage temperature	-55 to 150	°C
TJ	Operating junction temperature	-40 to 150	°C

Table 2. Absolute maximum rating
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#### Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJC</sub>	Thermal resistance junction-case max.	3.1	°C/W



# 2 Electrical characteristics

 $T_{case} = 25 \ ^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current $(V_{BE} = 0)$	V <sub>CE</sub> = 700 V V <sub>CE</sub> = 700 V	T <sub>C</sub> = 125 °C			1 5	mA mA
V <sub>(BR)EBO</sub>	Emitter-Base breakdown voltage (I <sub>C</sub> = 0)	l <sub>E</sub> = 10 mA		9		18	V
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	l <sub>C</sub> = 10 mA		400			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{C} = 0.5 \text{ A}$ $I_{C} = 1 \text{ A}$ $I_{C} = 1.5 \text{ A}$	l <sub>B</sub> = 0.25 A			0.5 1 1.5	V V V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 0.5 A I <sub>C</sub> = 1 A	-			1 1.2	V V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.5 A I <sub>C</sub> = 1 A		8 5		20 25	
t <sub>r</sub> t <sub>s</sub> t <sub>f</sub>	Resistive load Rise time Storage time Fall time	$V_{CC} = 125 V$ $I_{B1} = 0.2 A$ $t_p = 25 \mu s$	-			1 4 0.7	μs μs μs
t <sub>s</sub>	Inductive load Storage time	$I_{C} = 1 A$ $V_{BE} = -5 V$ $V_{Clamp} = 300 V$	L = 50  mH		0.8		μs

Table 4	Electrical	characteristics
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1. Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$  1.5%



GC57293

T<sub>C</sub> (℃)

#### 2.1 **Electrical characteristics (curves)**



Figure 4. Output characteristics





100

 $\mathsf{P}_{\mathsf{tot}}$ 



Figure 6. DC current gain ( $V_{CE} = 1 V$ )



Figure 7. DC current gain (V<sub>CE</sub> = 5 V)





Figure 9. Base-emitter saturation voltage

Figure 8. Collector-emitter saturation







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### 2.2 Test circuits



### Figure 12. Resistive load switching test circuit

- 1. Fast electronic switch
- 2. Non-inductive resistor



### Figure 13. Inductive load switching test circuit

- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier



## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.



Dim.	mm.				
	Min.	Тур.	Max.		
А	2.4		2.9		
В	0.64		0.88		
B1	0.39		0.63		
D	10.5		11.05		
E	7.4		7.8		
е	2.04	2.29	2.54		
e1	4.07	4.58	5.08		
L	15.3		16		
Р	2.9		3.2		
Q		3.8			
Q1	1		1.52		
H2		2.15			
I		1.27			

Table 5. SOT-32 (TO-126) mechanical data

### Figure 14. SOT-32 (TO-126) drawings





# 4 Revision history

Date	Revision	Changes	
23-May-2007	1	Initial release.	
09-Jul-2008	2	Added Table 1 on page 1.	
15-Dec-2009	3	Added Table 3: Thermal data on page 2.	
15-Jun-2011	4	Modified: Table 2	
18-Jun-2013	5	Added device ST13003.	

### Table 6. Document revision history



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